



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
30V	1.5Ω @ V _{GS} = 4.5V	0.4A
	2.0Ω @ V _{GS} = 2.5V	0.35A
	3.0Ω @ V _{GS} = 1.8V	0.3A
	4.5Ω @ V _{GS} = 1.5V	0.23A

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- General purpose interfacing switches
- · Power management functions
- Analog switches

Features and Benefits

- Low Package Profile, 0.4mm Maximum Package Height
- 0.48mm² Package Footprint, 16 Times Smaller Than SOT23
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V max
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

 https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: X2-DFN0806-3
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 4
- Weight: 0.001 grams (Approximate)

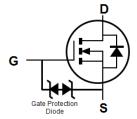
X2-DFN0806-3





Bottom View





Equivalent Circuit

Ordering Information (Note 4)

Part Number	Dookono	Packing		
	Package	Qty.	Carrier	
DMN31D5UFA-7B	X2-DFN0806-3	10K	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Top View

BZ = Product Type Marking Code
Bar Denotes Gate and Source Side



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	30	V
Gate-Source Voltage			Vgss	±12	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	0.4 0.37	А
Maximum Continuous Body Diode Forward Current (Note 5)			Is	0.32	Α
Pulsed Drain Current (Note 6)			I _{DM}	0.75	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	Steady State	PD	380	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	332	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

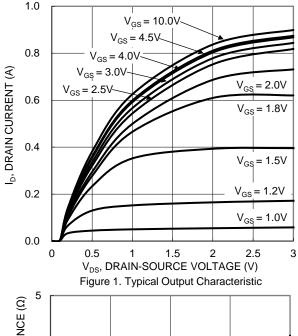
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			,,		l	1
Drain-Source Breakdown Voltage		30	_	_	V	V _G S = 0V, I _D = 250μA
Zero Gate Voltage Drain Current @Tc = +25°C		_	_	100	nA	V _{DS} = 24V, V _{GS} = 0V
Gate-Source Leakage		_	_	±10	μΑ	V _G S = ±10V, V _D S = 0V
ON CHARACTERISTICS (Note 7)						•
Gate Threshold Voltage	Vgs(TH)	0.4	_	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
		_	1.3	1.5	Ω	V _{GS} = 4.5V, I _D = 100mA
Static Drain-Source On-Resistance	Dagger	_	1.4	2.0		V _G S = 2.5V, I _D = 50mA
Static Dialii-Source Off-Resistance	RDS(ON)	_	1.6	3.0		V _G S = 1.8V, I _D = 20mA
		_	1.8	4.5		V _G S = 1.5V, I _D = 10mA
Diode Forward Voltage		0.4	0.6	1.0	V	V _{GS} = 0V, I _S = 10mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		15.4		pF	457777
Output Capacitance	Coss	_	8	_	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	5	_	pF	1 - 1.000112
Total Gate Charge	Qg	_	0.3	_	nC	V 45V V 45V
Gate-Source Charge	Qgs	_	0.05	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$ $I_{D} = 200mA$
Gate-Drain Charge	Qgd		0.1		nC	10 – 20011A
Turn-On Delay Time	t _{D(ON)}		5.7		ns	
Turn-On Rise Time Turn-Off Delay Time		_	9.1	_	ns	V _{DD} = 15V, V _{GS} = 4.5V,
			146		ns	$R_G = 2\Omega$, $I_D = 200 \text{mA}$
Turn-Off Fall Time	t _F		48		ns	

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.





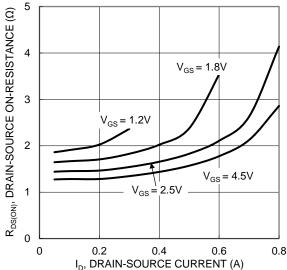


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

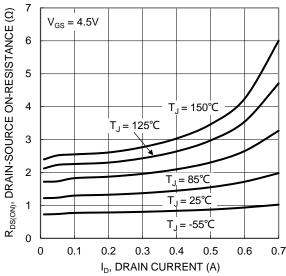
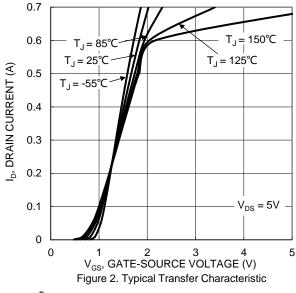
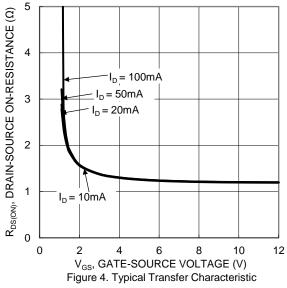


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





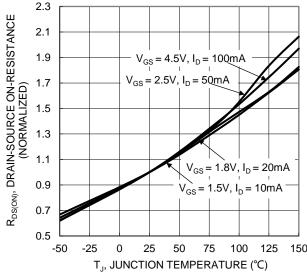


Figure 6. On-Resistance Variation with Junction Temperature





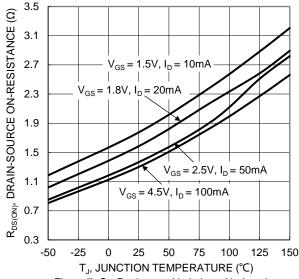


Figure 7. On-Resistance Variation with Junction Temperature

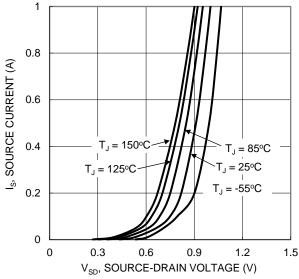


Figure 9. Diode Forward Voltage vs. Current

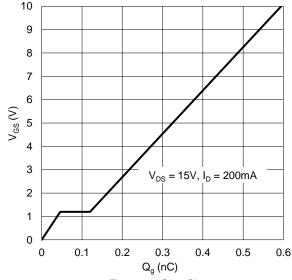


Figure 11. Gate Charge

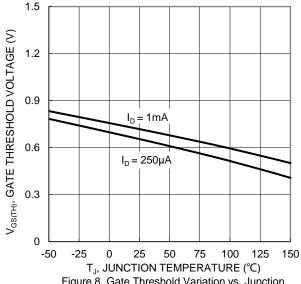
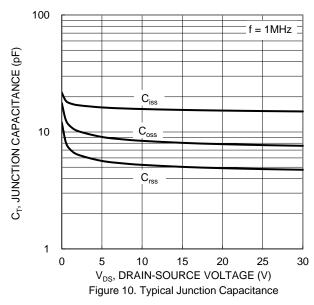
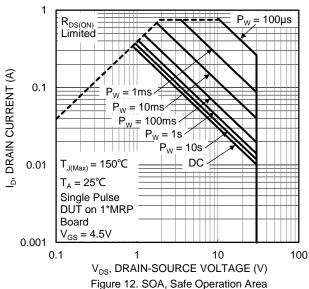


Figure 8. Gate Threshold Variation vs. Junction Temperature







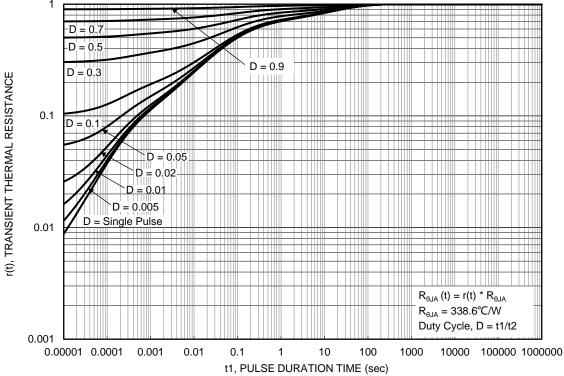


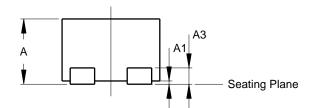
Figure 13. Transient Thermal Resistance

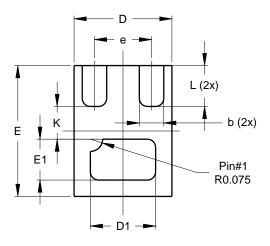


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0806-3



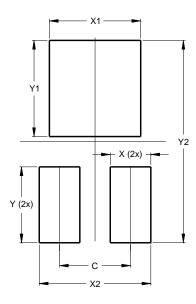


X2-DFN0806-3					
Dim	Min	Max	Тур		
Α	0.375	0.40	0.39		
A1	0	0.05	0.02		
A3	-	-	0.10		
b	0.10	0.20	0.15		
D	0.55	0.65	0.60		
D1	0.35	0.45	0.40		
Е	0.75	0.85	0.80		
E1	0.20	0.30	0.25		
е	-	-	0.35		
K	-	-	0.20		
Ĺ	0.20	0.30	0.25		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0806-3



Dimensions	Value (in mm)		
С	0.350		
Х	0.200		
X1	0.450		
X2	0.550		
Y	0.375		
Y1	0.475		
Y2	1.000		



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